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N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
30	$0.0036 \text{ at V}_{GS} = 10 \text{ V}$	70 ^d	67		
30	0.0044 at V _{GS} = 4.5 V	70 ^d	07		





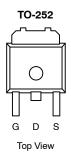
TrenchFET® Power MOSFET

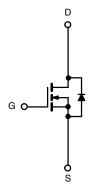
100 % R_q and UIS Tested

Compliant to RoHS Directive 2002/95/EC

COMPLIANT HALOGEN FREE







N-Channel MOSFET

APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- DC/DC Converter

ABSOLUTE MAXIMUM RATINGS	$T_C = 25 ^{\circ}C$, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C	I-	70 ^d		
Continuous Diam Current (1) = 130 C)	T _C = 70 °C	I _D	60 ^d	A	
Pulsed Drain Current	I _{DM}	120	7 ^		
Avalanche Current		I _{AS}	45	1	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	101	mJ	
Mariana Parana Disabational	T _C = 25 °C	P _D	78.1 ^b	W	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	T P	3.1		
Operating Junction and Storage Temperature Ra	inge	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1.6	C/VV		

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30		V		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1 2.5		V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 30 V, V_{GS} = 0 V, T_J = 125 °C			50	μΑ	
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ}\text{C}$			250	1	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
	B	V _{GS} = 10 V, I _D = 22 A		0.0030	0.0036	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0036	0.0044		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		110		S	
Dynamic ^b							
Input Capacitance	C _{iss}			3535		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$		680			
Reverse Transfer Capacitance	C _{rss}			400			
Total Gate Charge ^c	Qg			67	100		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		10.5		nC	
Gate-Drain Charge ^c	Q_{gd}			12.2			
Gate Resistance	R _g	f = 1 MHz	0.3	1.4	2.8	Ω	
Turn-On Delay Time ^c	t _{d(on)}			11	20		
Rise Time ^c	t _r	V_{DD} = 15 V, R_L = 1.5 Ω		10	20	no	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		35	53	ns ns	
Fall Time ^c	t _f			10	20		
Drain-Source Body Diode Ratings ar	nd Characteris	stics T _C = 25 °C ^b					
Continuous Current	I _S				70	^	
Pulsed Current	I _{SM}			120		Α	
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V		0.83	1.5	V	
Reverse Recovery Time	t _{rr}			41	62	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	$I_F = 10 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		2	3	Α	
Reverse Recovery Charge	Q _{rr}			40	60	nC	

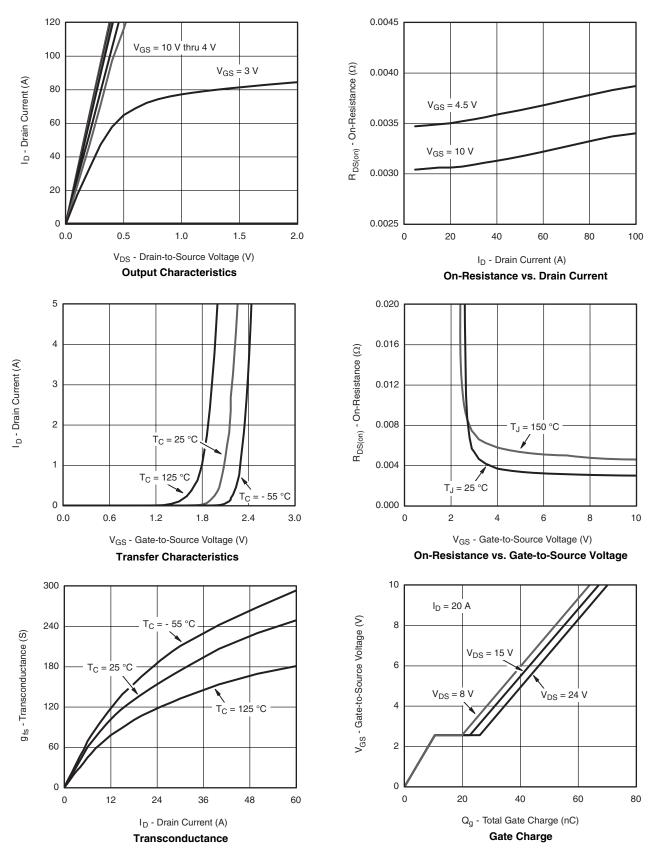
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

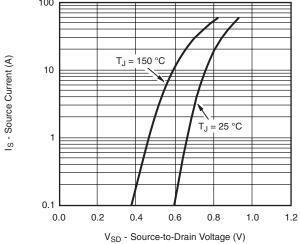


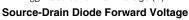
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

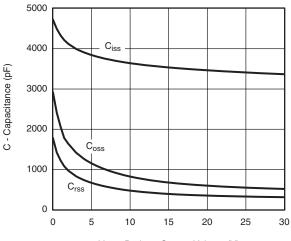


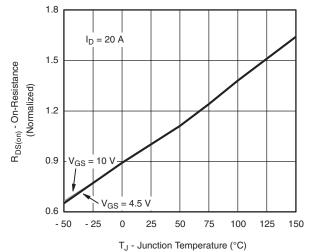


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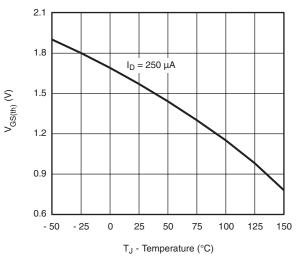




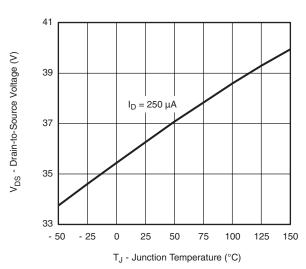




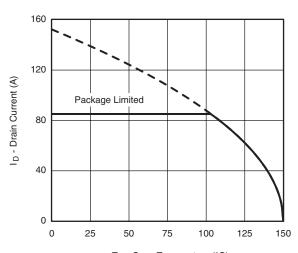
On-Resistance vs. Junction Temperature



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



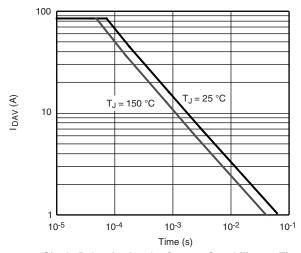
T_C - Case Temperature (°C)

Current Derating

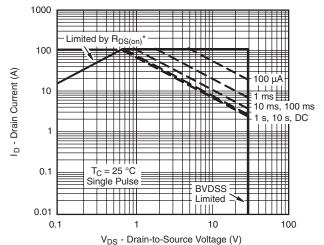




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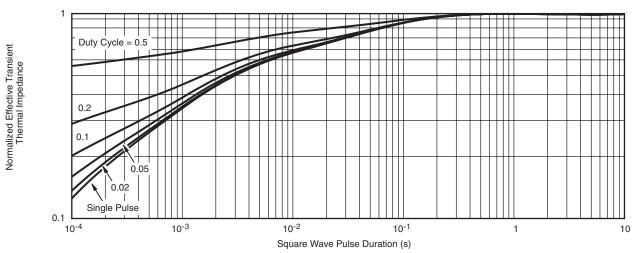


Single Pulse Avalanche Current Capability vs. Time



* $V_{GS} > \mbox{minimum } V_{GS}$ at which $R_{DS(on)}$ is specified

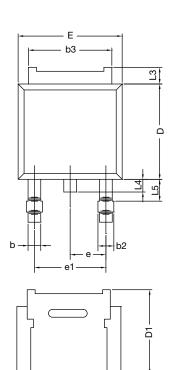
Safe Operating Area



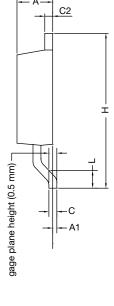
Normalized Thermal Transient Impedance, Junction-to-Case



TO-252AA CASE OUTLINE



E1



	MILLIN	METERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC		0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
FCN: X12-0247-Rev. M. 24-Dec-12					

ECN: X12-0247-Rev. M, 24-Dec-12

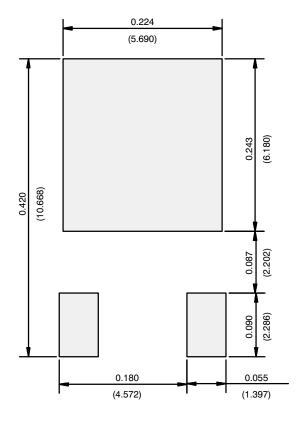
DWG: 5347

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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